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Attorney Docket No. 5649-874

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Hag-ju Cho  
Serial No.: 09/893,035 ✓  
Filed: June 27, 2001  
For:

Confirmation No. 3421  
Examiner: Erik J. Kielin  
Group Art Unit: 2813

METHODS OF MANUFACTURING INTEGRATED CIRCUIT DEVICES  
THAT INCLUDE A METAL OXIDE LAYER DISPOSED ON ANOTHER  
LAYER TO PROTECT THE OTHER LAYER FROM DIFFUSION OF  
IMPURITIES AND INTEGRATED CIRCUIT DEVICES MANUFACTURED  
USING SAME

Date: January 30, 2003

BOX RCE  
Commissioner for Patents  
Washington, DC 20231

**AMENDMENT ACCOMPANYING RCE**

Sir:

This Amendment is responsive to the Final Official Action of October 2, 2002 and the Advisory Action of January 16, 2003. Pursuant to the rules for amendments under 37 C.F.R. § 1.121, the claims have been amended herein using the rewritten claims format. The present amendment also includes a section entitled "**VERSION WITH MARKINGS TO SHOW CHANGES MADE**" attached hereto.

**In the claims:**

Please enter amended Claim 1 as follows:

C1

1. (Amended) A method of manufacturing an integrated circuit device, comprising:

forming an insulation layer that comprises oxygen between upper and lower conductive layers, the insulation layer having a first surface portion that is exposed by the upper and lower conductive layers and a second, non-exposed, surface portion; and

exposing the insulation layer to a metal precursor that is reactive with oxygen so as to form a first metal oxide layer on the first surface portion of the insulation layer without forming the first metal oxide layer on the second surface portion of the insulation layer, such that the first metal oxide layer and the second surface portion of the insulation layer do not overlap.

Handwritten mark: a stylized 'A' or 'B' with a diagonal line.